

SMALL-SIGNAL TRANSISTORS — PLASTIC (continued)

Central Collector 800 MW TO-92

The transistors listed in this table have been designed to provide power dissipation. These devices are listed in order of decreasing breakdown voltage (BVCEO).

Device Type	BV _{CEO} Volts Min.	I _C Amp Cont.	h _{FE} Min. @ I _C mA	V _{CE(sat)} Volts Max. @ I _C mA	I _B mA	f _T MHz Min. @ I _C mA	PIN OUT
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NPN

BF420	300	0.1	40	25	2.0	20	2	60	10	ECB
BF422	250	0.1	50	25	2.0	20	2	60	10	ECB
BC639	80	1.0	40	150	0.5	500	50	60	10	ECB
BC637	60	1.0	40	150	0.5	500	50	60	10	ECB
BC635	45	1.0	40	150	0.5	500	50	60	10	ECB
BC368	20	1.0	60	1000	0.5	1000	100	65	10	ECB

PNP

BF421	300	0.1	40	25	2.0	20	2	60	10	ECB
BF423	250	0.1	50	25	2.0	20	2	60	10	ECB
BC640	80	1.0	40	150	0.5	500	50	60	10	ECB
BC639	60	1.0	40	150	0.5	500	50	60	10	ECB
BC636	45	1.0	40	150	0.5	500	50	60	10	ECB
BC369	20	1.0	60	1000	0.5	1000	100	65	10	ECB

Telecom Transistors (TO92)

These devices are special product ranges intended for use in Telecom application which require an excellent long term reliability.

NPN DEVICES	PNP DEVICES	BV _{CEO} V	PD _{mW} 25°C Amb	I _C (mA) Cont	HFE				F _T Min MHz	PIN OUT
					min	max	I _C (mA)	V _{CE} (V)		
P2N2222		30	625	600	75	—	10	10	250	CBE
P2N2222A		40	625	600	75	—	10	10	300	CBE
(1)PBF259,S (1)PBF259R,RS	P2N2907	40	625	600	75	—	10	10	200	CBE
	P2N2907A	60	625	600	100	—	10	10	200	CBE
		300	625	500	25	—	1	10	40	EBC
		300	625	500	25	—	1	10	40	CBE
	(2)PBF493,S	300	625	500	40	—	1	10	40	EBC
	(2)PBF493R,RS	300	625	500	40	—	1	10	40	CBE

(1) "S" version, HFE Min 60 @ I_C = 20 mA, V_{CE} = 10 V.

(2) "S" version, HFE Min 40 @ I_C = 0.1 mA, V_{CE} = 1 V.